1.(original) A thin film capacitor/inductor/interconnect method comprising:

(a) thinly metalizing a substrate with a lower electrode and interconnect layer formed on said thin film hybrid substrate, said layer further comprising a lower adhesive layer and an upper conducting layer having a sum total thickness of less than or equal to 1.5 microns;

(b) applying/imaging photoresist and etching to form metal patterns on said substrate for lower capacitor electrodes and interconnect;

(c) applying a thin dielectric layer to said metal patterns;

(d) applying/imaging photoresist and etching to form contact holes in said dielectric layer and optionally selectively patterning said dielectric layer;

(e) metalizing said substrate to make contact with said lower capacitor electrodes and interconnect;

(f) applying/imaging photoresist and etching to form patterns for upper capacitor electrodes, inductors, and/or interconnect conductors;

(g) optionally forming resistor elements by applying/imaging photoresist and etching a resistor layer on said substrate;

wherein

said upper conducting layer is approximately 0.25 microns thick.

2.(original) The thin film hybrid substrate method of Claim 1, wherein said lower adhesive layer is approximately 0.03 to 0.05 microns thick.

3.(original) The thin film hybrid substrate method of Claim 1, wherein said lower adhesive layer comprises chrome.

4.(original) The thin film hybrid substrate method of Claim 1, wherein said lower adhesive layer comprises titanium.

5.(original) The thin film hybrid substrate method of Claim 1, wherein said lower adhesive layer comprises titanium-tungsten.

6.(original) The thin film hybrid substrate method of Claim 1, wherein said upper conducting layer comprises silver.

7.(original) The thin film hybrid substrate method of Claim 1, wherein said upper conducting layer comprises aluminum.

8.(original) The thin film hybrid substrate method of Claim 1, wherein said upper conducting layer comprises gold.

9.(original) The thin film hybrid substrate method of Claim 1, wherein said upper conducting layer comprises copper.

10.(original) The thin film hybrid substrate method of Claim 1, wherein said lower electrode and interconnect layer further comprises silver.

11.(original) The thin film hybrid substrate method of Claim 1, wherein said lower electrode and interconnect layer further comprises aluminum.

12.(original) The thin film hybrid substrate method of Claim 1, wherein said lower electrode and interconnect layer further comprises gold.

13.(original) The thin film hybrid substrate method of Claim 1, wherein said lower electrode and interconnect layer further comprises copper.

14.(original) The thin film hybrid substrate method of Claim 1, wherein said lower electrode and interconnect layer is selected from the group consisting of tantalum, tungsten, titanium, nickel, molybdenum, platinum, palladium, and chromium.

15.(original) The thin film hybrid substrate method of Claim 1, wherein said dielectric layer is selectively patterned.

16. The thin film hybrid substrate method of Claim 1, wherein said dielectric layer further comprises silicon nitride.

17.(original) The thin film hybrid substrate method of Claim 1, wherein said dielectric layer further comprises silicon dioxide.

18.(original) The thin film hybrid substrate method of Claim 1, wherein said dielectric layer further comprises silicon oxynitride.

19.(original) The thin film hybrid substrate method of Claim 1, wherein said dielectric layer further comprises aluminum oxide.

20.(original) The thin film hybrid substrate method of Claim 1, wherein said dielectric layer further comprises tantalum pentoxide.

21.(original) The thin film hybrid substrate method of Claim 1, wherein said dielectric layer further comprises a ferroelectric material.

22. The thin film hybrid substrate method of Claim 21, wherein said ferroelectric material is $BaTiO_3$.

23.(original) The thin film hybrid substrate method of Claim 21, wherein said ferroelectric material is $SrTiO_3$.

24.(original) The thin film hybrid substrate method of Claim 21, wherein said ferroelectric material is $PbZrO_3$.

25.(original) The thin film hybrid substrate method of Claim 21, wherein said ferroelectric material is $PbTiO_3$.

26.(original) The thin film hybrid substrate method of Claim 21, wherein said ferroelectric material is $LiNbO_3$.

27.(original) The thin film hybrid substrate method of Claim 21, wherein said ferroelectric material is $Bi_{14}Ti_3O_{12}$.

28.(original) The thin film hybrid substrate method of Claim 1, wherein said dielectric layer further comprises polyimide.

29. (original) The thin film hybrid substrate method of Claim 1, wherein said dielectric layer further comprises benzocyclobutene.

30. (original) The thin film hybrid substrate method of Claim 1, wherein said substrate material is selected from the group consisting of alumina, beryllium oxide, fused silica, aluminum nitride, sapphire, ferrite, diamond, LTCC, and glass.

Claims 31-67 (cancelled).